



NEC's NPN SiGe RF TRANSISTOR FOR MEDIUM OUTPUT POWER AMPLIFICATION (800 mW) 3-PIN POWER MINIMOLD (34 PACKAGE)

NESG250134

FEATURES

- **THIS PRODUCT IS SUITABLE FOR
MEDIUM OUTPUT POWER (800 mW) AMPLIFICATION**
 $P_O = 29 \text{ dBm TYP. @ } V_{CE} = 3.6 \text{ V, } P_{in} = 15 \text{ dBm, } f = 460 \text{ MHz}$
 $P_O = 29 \text{ dBm TYP. @ } V_{CE} = 3.6 \text{ V, } P_{in} = 20 \text{ dBm, } f = 900 \text{ MHz}$
- **MAXIMUM STABLE GAIN:**
 $MSG = 23 \text{ dB TYP @ } V_{CE} = 3.6 \text{ V, } I_C = 100 \text{ mA, } f = 460 \text{ MHz}$
- **SiGe TECHNOLOGY:**
UHS2-HV process
- **ABSOLUTE MAXIMUM RATINGS:**
 $V_{CBO} = 20 \text{ V}$
- **3-PIN POWER MINIMOLD (34 PACKAGE)**

ORDERING INFORMATION

PART NUMBER	ORDER NUMBER	PACKAGE	QUANTITY	SUPPLYING FORM
NESG250134	NESG250134-AZ	3-pin power minimold	25 pcs (Non reel)	• 12 mm wide embossed taping • Pin 2 (Emitter) face the perforation side of the tape
NESG250134-T1	NESG250134-T1-AZ	(Pb-Free) ^{Note1}	1 kpcs/reel	

Note 1. Contains lead in the part except the electrode terminals.

Remark To order evaluation samples, contact your nearby sales office.
Unit sample quantity is 25 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector to Base Voltage	V_{CBO}	20	V
Collector to Emitter Voltage	V_{CEO}	9.2	V
Emitter to Base Voltage	V_{EBO}	2.8	V
Collector Current	I_C	500	mA
Total Power Dissipation	P_{tot} ^{Note}	1.5	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

Note Mounted on $34.2 \text{ cm}^2 \times 0.8 \text{ mm (t)}$ glass epoxy PWB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

THERMAL RESISTANCE (T_A = 25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Thermal Resistance from Junction to Ambient ^{Note}	R _{thj-a}	80	°C/W

Note Mounted on 34.2 cm² × 0.8 mm (t) glass epoxy PWB

RECOMMENDED OPERATING RANGE (T_A = 25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector to Emitter Voltage	V _{CE}	–	3.6	4.5	V
Collector Current	I _C	–	400	500	mA
Input Power ^{Note}	P _{in}	–	12	17	dBm

Note Input power under conditions of V_{CE} ≤ 4.5 V, f = 460 MHz

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
DC Characteristics						
Collector Cut-off Current	I_{CBO}	$V_{CB} = 5\text{ V}, I_E = 0\text{ mA}$	–	–	1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 0.5\text{ V}, I_C = 0\text{ mA}$	–	–	1	μA
DC Current Gain	h_{FE} ^{Note 1}	$V_{CE} = 3\text{ V}, I_C = 100\text{ mA}$	80	120	180	–
RF Characteristics						
Gain Bandwidth Product	f_T	$V_{CE} = 3.6\text{ V}, I_C = 100\text{ mA}, f = 460\text{ MHz}$	–	10	–	GHz
Insertion Power Gain	$ S_{21} ^2$	$V_{CE} = 3.6\text{ V}, I_C = 100\text{ mA}, f = 460\text{ MHz}$	–	19	–	dB
Maximum Stable Gain	MSG ^{Note 2}	$V_{CE} = 3.6\text{ V}, I_C = 100\text{ mA}, f = 460\text{ MHz}$	–	23	–	dB
Linear gain (1)	G_L	$V_{CE} = 3.6\text{ V}, I_{C(\text{set})} = 30\text{ mA (RF OFF)}, f = 460\text{ MHz}, P_{in} = 0\text{ dBm}$	16	19	–	dB
Linear gain (2)	G_L	$V_{CE} = 3.6\text{ V}, I_{C(\text{set})} = 30\text{ mA (RF OFF)}, f = 900\text{ MHz}, P_{in} = 0\text{ dBm}$	–	16	–	dB
Output Power (1)	P_O	$V_{CE} = 3.6\text{ V}, I_{C(\text{set})} = 30\text{ mA (RF OFF)}, f = 460\text{ MHz}, P_{in} = 15\text{ dBm}$	27	29	–	dBm
Output Power (2)	P_O	$V_{CE} = 3.6\text{ V}, I_{C(\text{set})} = 30\text{ mA (RF OFF)}, f = 900\text{ MHz}, P_{in} = 20\text{ dBm}$	–	29	–	dBm
Collector Efficiency (1)	η_c	$V_{CE} = 3.6\text{ V}, I_{C(\text{set})} = 30\text{ mA (RF OFF)}, f = 460\text{ MHz}, P_{in} = 15\text{ dBm}$	–	60	–	%
Collector Efficiency (2)	η_c	$V_{CE} = 3.6\text{ V}, I_{C(\text{set})} = 30\text{ mA (RF OFF)}, f = 900\text{ MHz}, P_{in} = 20\text{ dBm}$	–	60	–	%

Notes 1. Pulse measurement: $PW \leq 350\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$

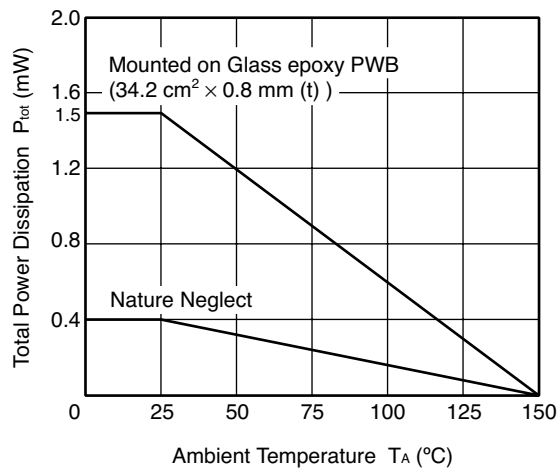
$$2. MSG = \left| \frac{S_{21}}{S_{12}} \right|$$

h_{FE} CLASSIFICATION

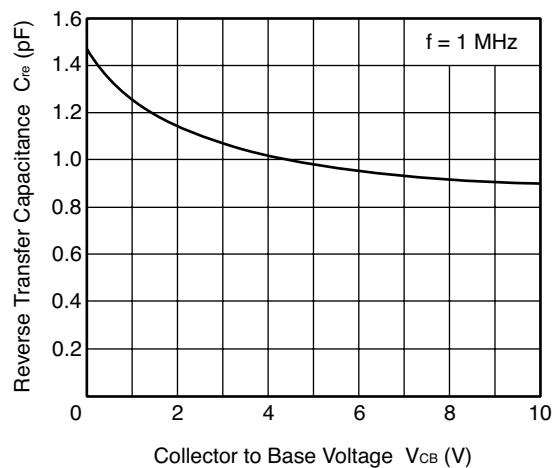
RANK	FB
Marking	SN
h_{FE} Value	80 to 180

TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

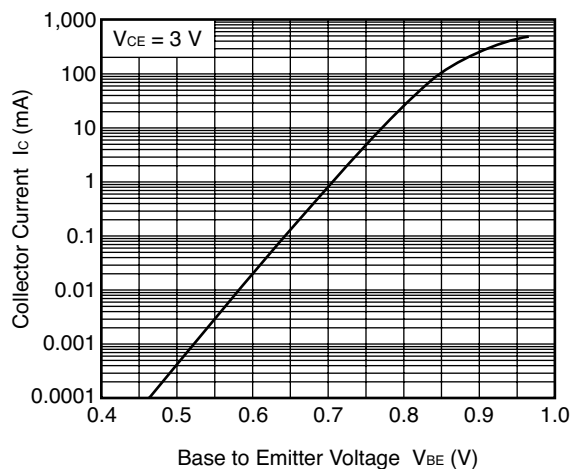
TOTAL POWER DISSIPATION
vs. AMBIENT TEMPERATURE



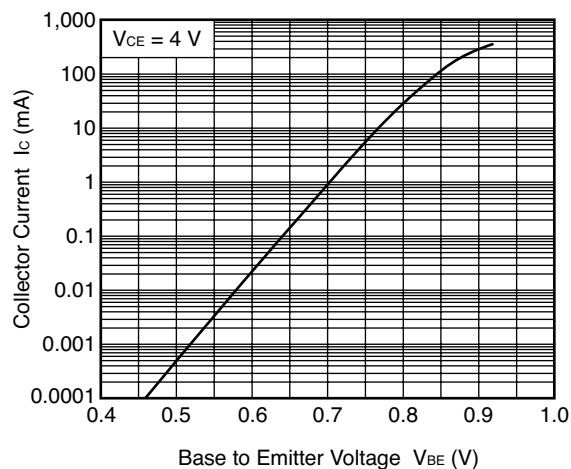
REVERSE TRANSFER CAPACITANCE
vs. COLLECTOR TO BASE VOLTAGE



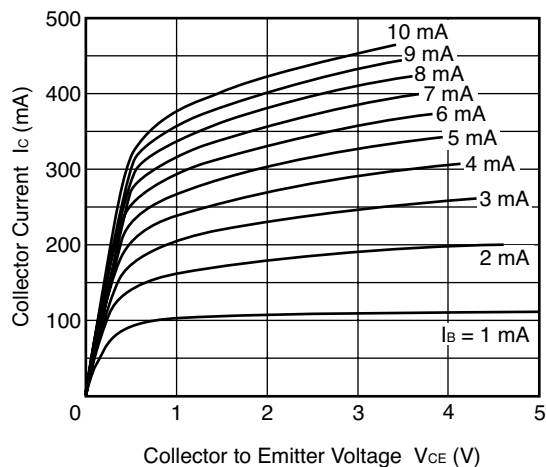
COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE



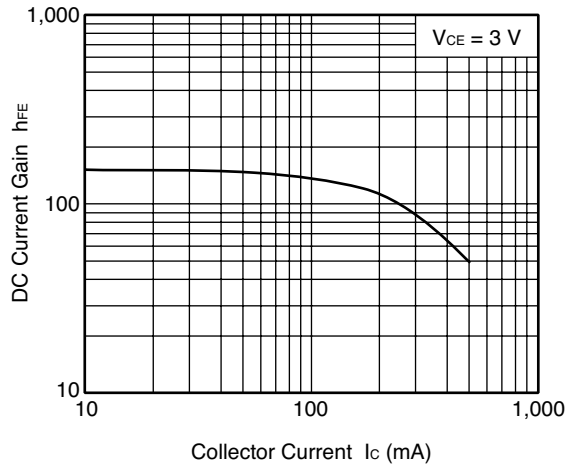
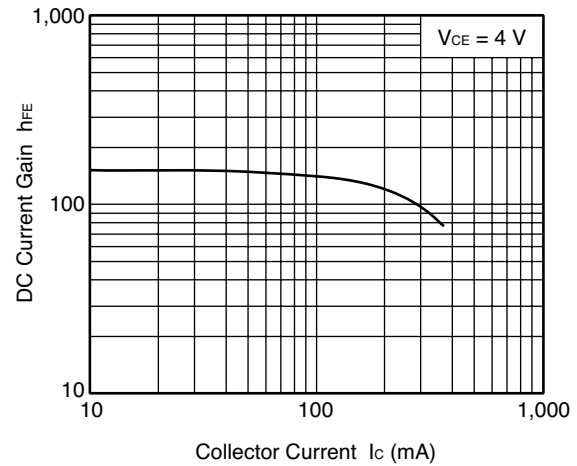
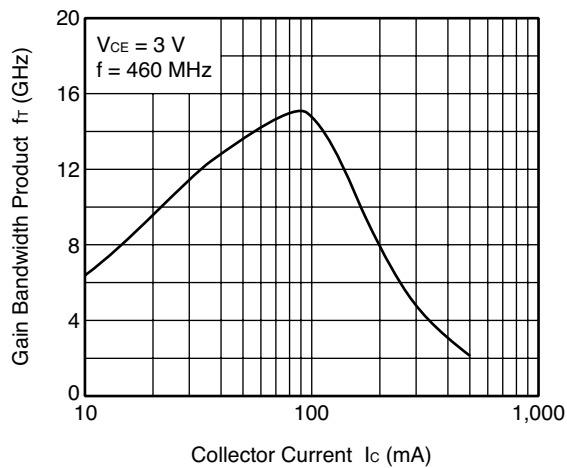
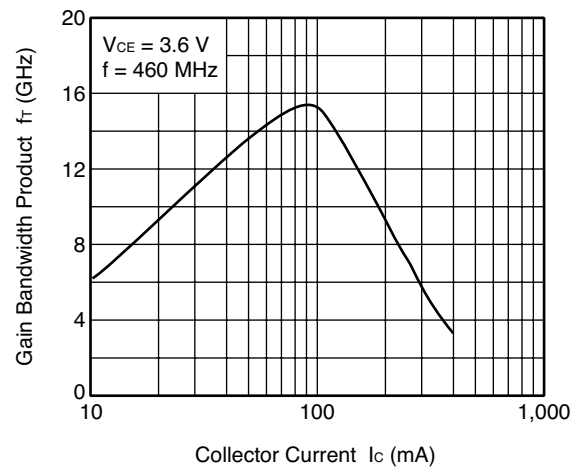
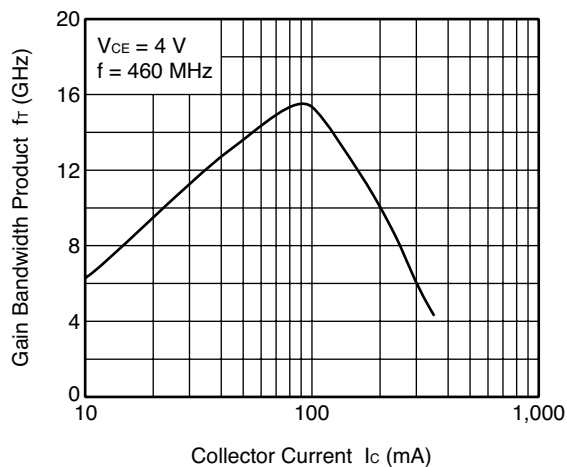
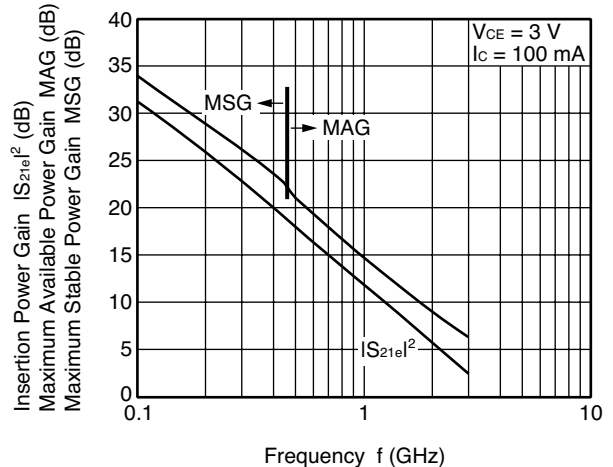
COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE



COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE

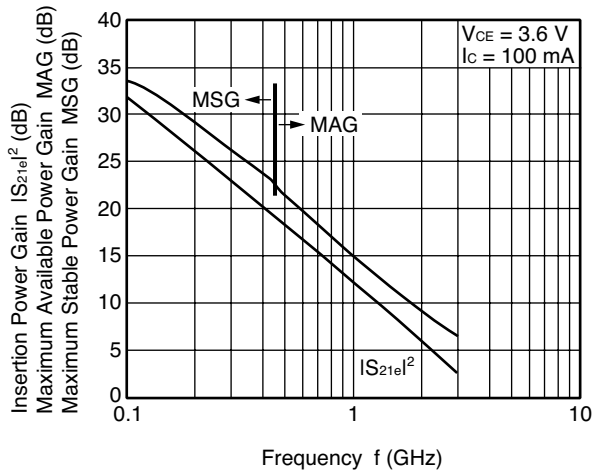


Remark The graphs indicate nominal characteristics.

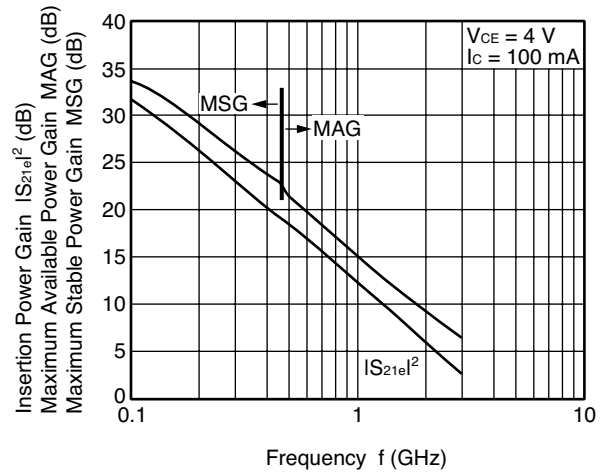
DC CURRENT GAIN vs.
COLLECTOR CURRENTDC CURRENT GAIN vs.
COLLECTOR CURRENTGAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENTGAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENTGAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENTINSERTION POWER GAIN,
MAG, MSG vs. FREQUENCY

Remark The graphs indicate nominal characteristics.

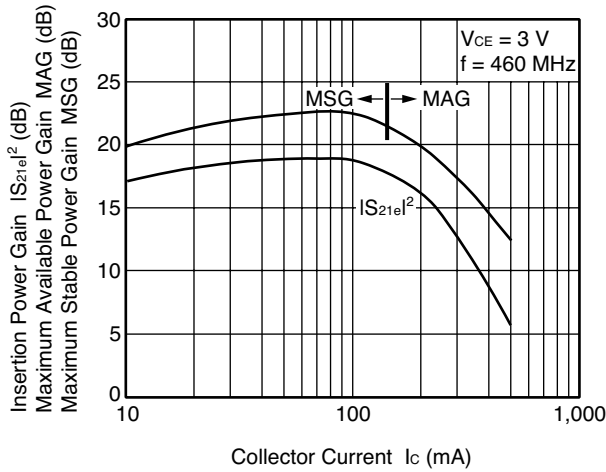
INSERTION POWER GAIN,
MAG, MSG vs. FREQUENCY



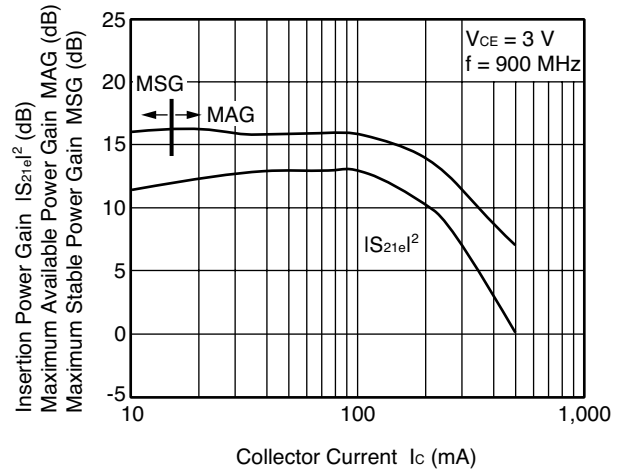
INSERTION POWER GAIN,
MAG, MSG vs. FREQUENCY



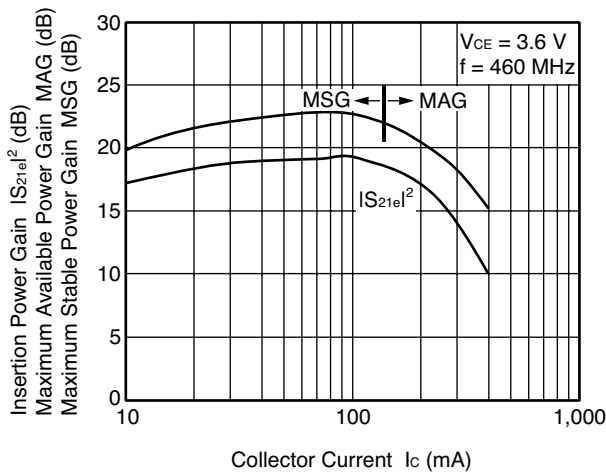
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



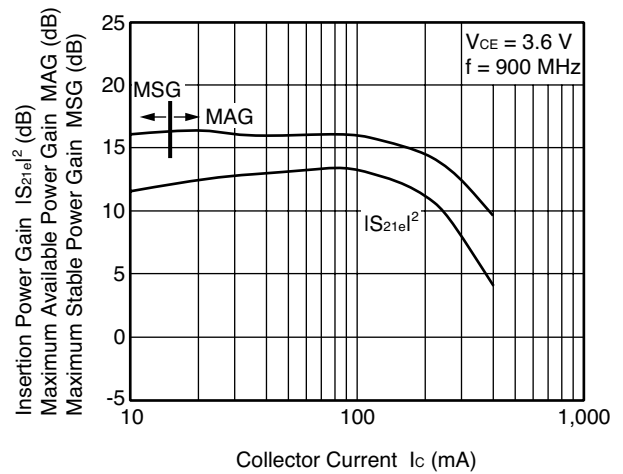
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT

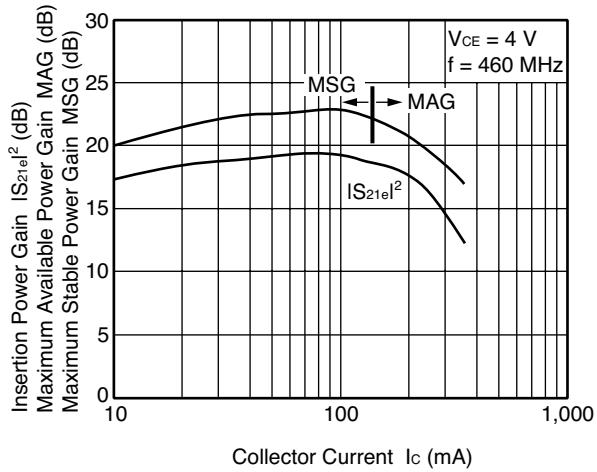


INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT

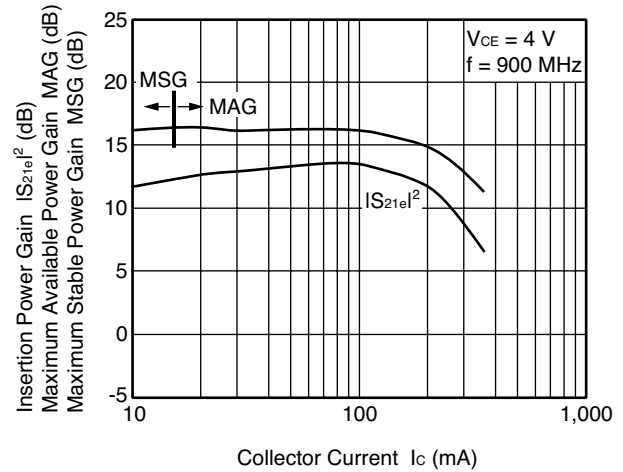


Remark The graphs indicate nominal characteristics.

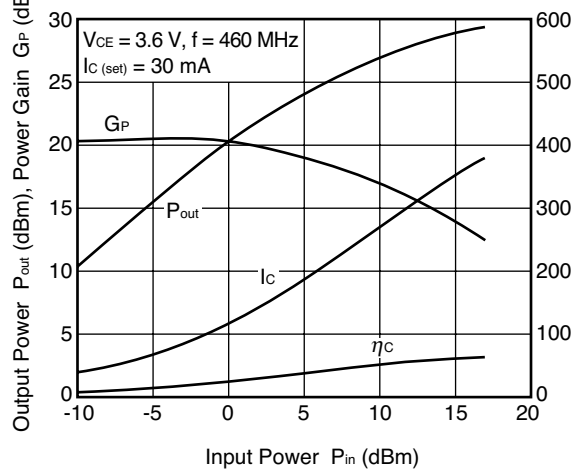
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



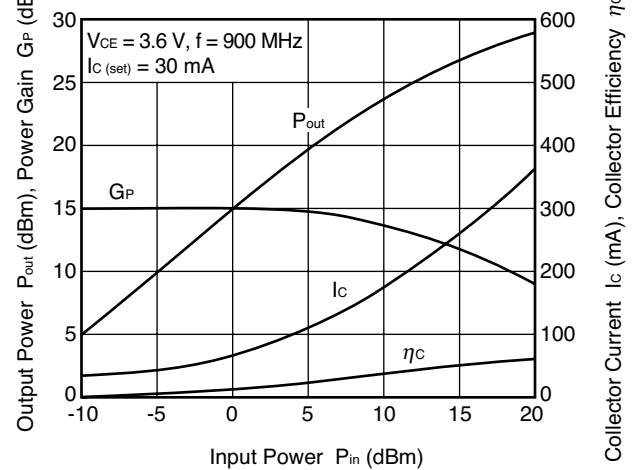
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



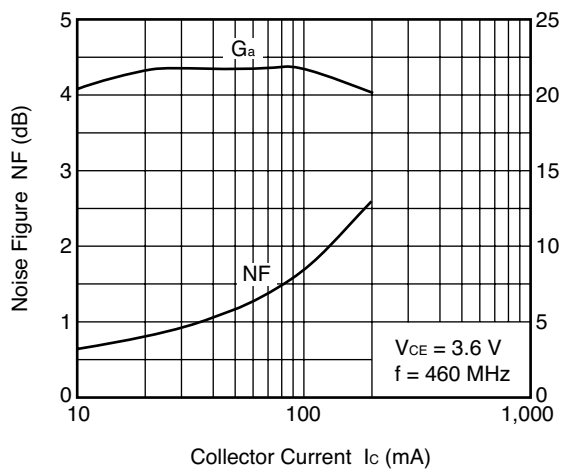
OUTPUT POWER, POWER GAIN,
COLLECTOR CURRENT, COLLECTOR
EFFICIENCY vs. INPUT POWER



OUTPUT POWER, POWER GAIN,
COLLECTOR CURRENT, COLLECTOR
EFFICIENCY vs. INPUT POWER



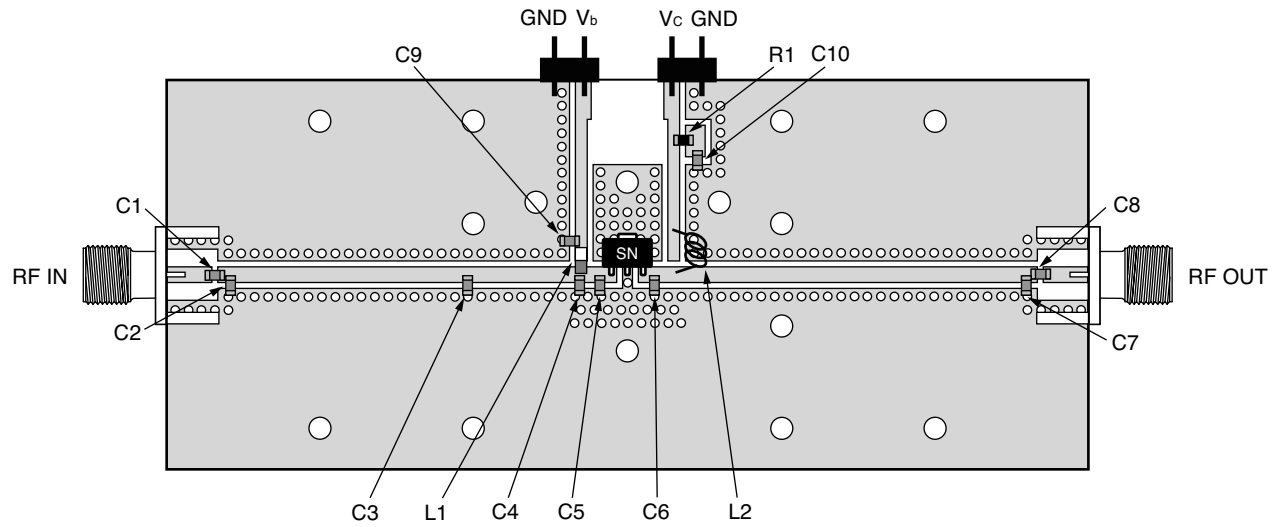
NOISE FIGURE, ASSOCIATED GAIN
vs. COLLECTOR CURRENT



Associated Gain G_a (dB)

Remark The graphs indicate nominal characteristics.

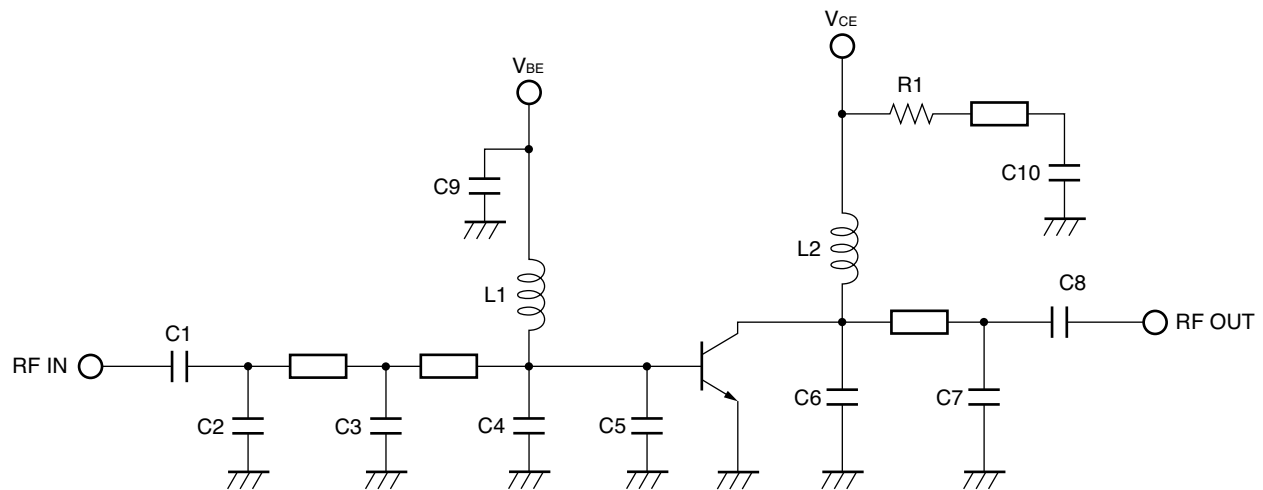
PA EVALUATION BOARD (f = 460 MHz)



Notes

1. 38 × 90 mm, t = 0.8 mm double sided copper clad glass epoxy PWB.
2. Back side: GND pattern
3. Solder gold plated on pattern
4. ○: Through holes

PA EVALUATION CIRCUIT (f = 460 MHz)

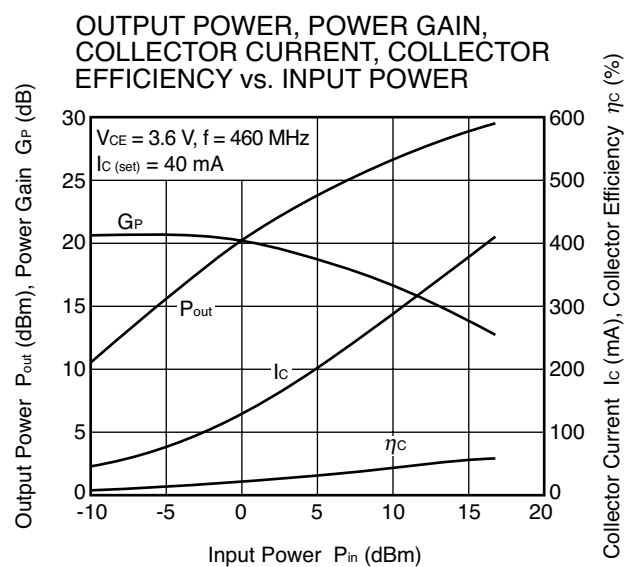


The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

COMPONENT LIST

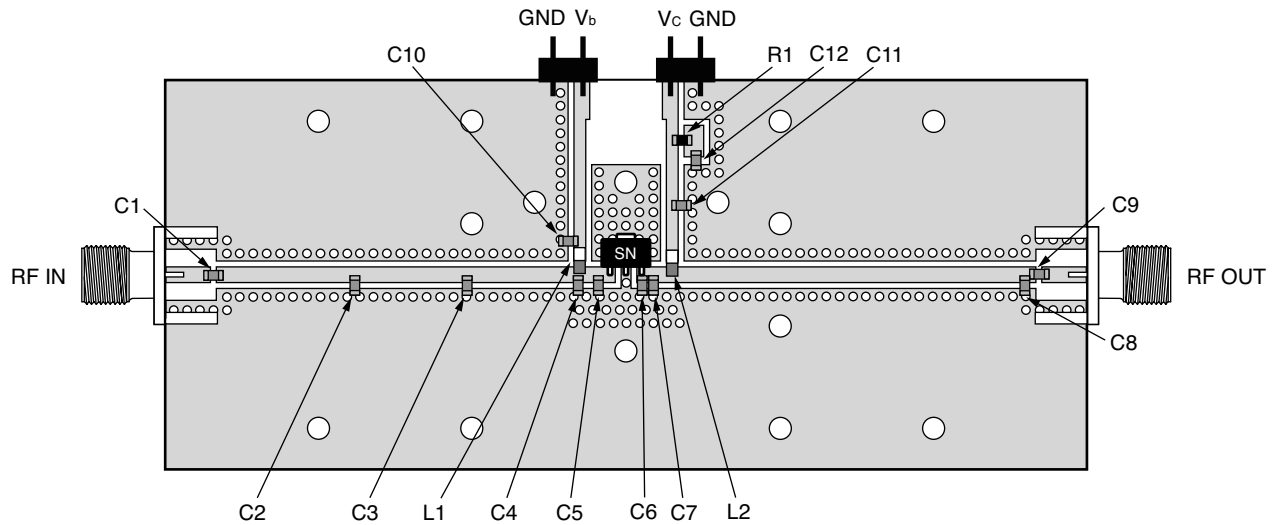
	VALUE	MAKER
C1	30 pF	Murata
C2	6 pF	Murata
C3, C4	7 pF	Murata
C5	3 pF	Murata
C6	0.5 pF	Murata
C7	5 pF	Murata
C8	10 pF	Murata
C9, C10	100 nF	Murata
L1	100 nH	Toko
L2	3 nH	Toko
R1	30 Ω	SSM

PA EVALUATION CIRCUIT TYPICAL CHARACTERISTICS



Remark The graphs indicate nominal characteristics.

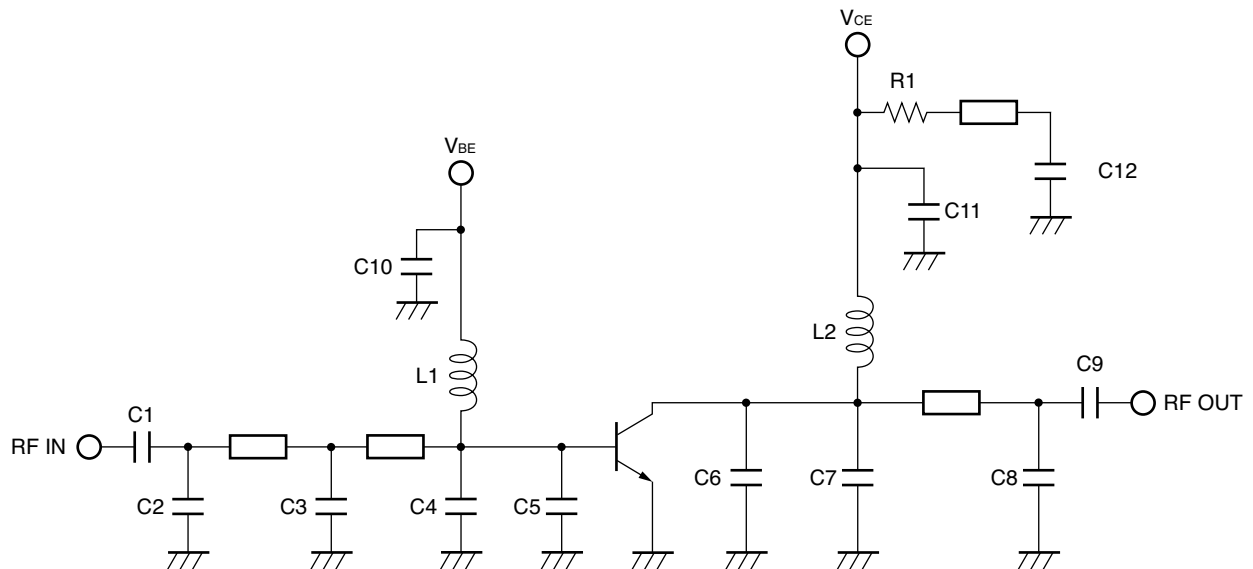
DISTORTION EVALUATION BOARD (f = 460 MHz)



Notes

1. 38 × 90 mm, t = 0.8 mm, double sided copper clad glass epoxy PWB.
2. Back side: GND pattern
3. Solder gold plated on pattern
4. ○○: Through holes

DISTORTION EVALUATION CIRCUIT (f = 460 MHz)

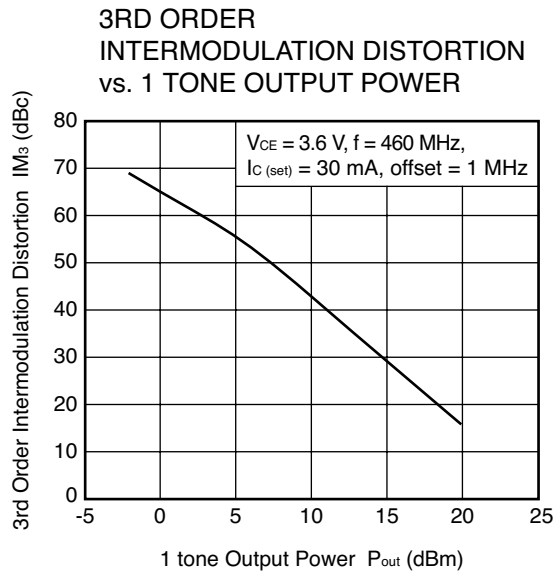


The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

COMPONENT LIST

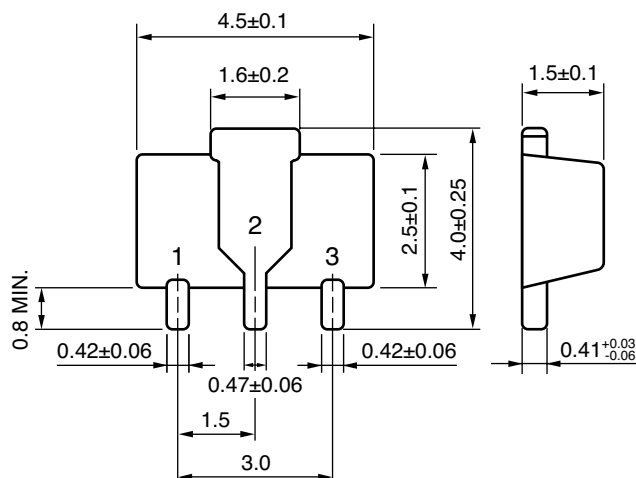
	VALUE	MAKER
C1	47 pF	Murata
C2	12 pF	Murata
C3, C4	7 pF	Murata
C5	3 pF	Murata
C6	6 pF	Murata
C7	0.5 pF	Murata
C8	5 pF	Murata
C9	51 pF	Murata
C10, C12	100 nF	Murata
C11	1 μ F	Murata
L1	100 nH	Toko
L2	15 nH	Toko
R1	30 Ω	SSM

DISTORTION EVALUATION CIRCUIT TYPICAL CHARACTERISTICS



Remark The graphs indicate nominal characteristics.

3-PIN POWER MINIMOLD (34 PACKAGE) (UNIT:mm)



PIN CONNECTIONS

1. Collector
2. Emitter
3. Base

Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

CEL California Eastern Laboratories, Your source for NEC RF, Microwave, Optoelectronic, and Fiber Optic Semiconductor Devices.
4590 Patrick Henry Drive • Santa Clara, CA 95054-1817 • (408) 988-3500 • FAX (408) 988-0279 • www.cel.com

DATA SUBJECT TO CHANGE WITHOUT NOTICE

03/07/2005